Symposium (Oral) | Symposium (technical) | Etching Technology for Nitride Semiconductors: recent progress in high-controllable and low-damaging process

[20p-E301-1~9]Etching Technology for Nitride Semiconductors: recent progress in high-controllable and low-damaging process

Masashi Kato(Nagoya Inst. of Tech.), Taketomo Sato(Hokkaido Univ.)

Fri. Sep 20, 2019 1:30 PM - 5:35 PM E301 (E301)

 \triangle : Presentation by Applicant for JSAP Young Scientists Presentation Award

▲ : English Presentation

▼: Both of Above

No Mark: None of Above

1:30 PM - 1:35 PM

[20p-E301-1]Introductory Talk

OTaketomo Sato¹ (1.Hokkaido Univ.)

Keywords:GaN etching